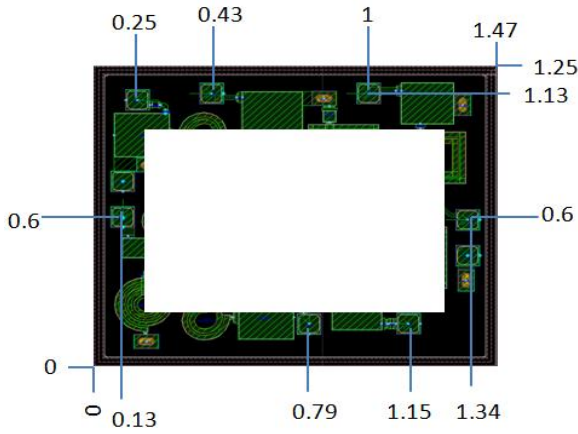


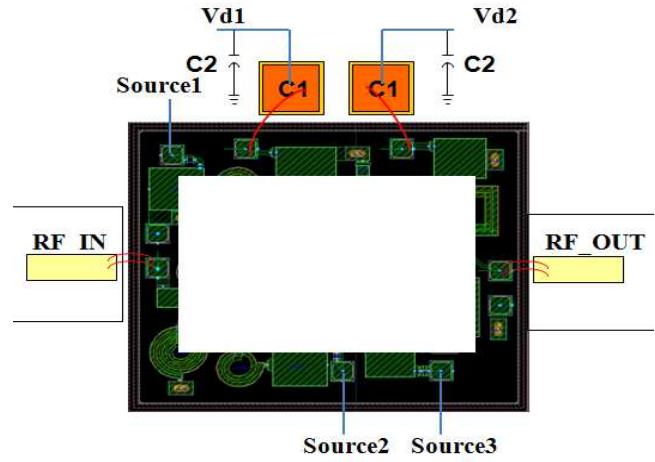
GaAs monolithic integrated low noise amplifier

7~11GHz

Shape and port size (mm)



Recommended assembly drawing



Assembly table

Pad	connect
V_{D1}, V_{D2}	Self-biased structure, both nodes must be connected to the power supply
Source 1/2/3	Adjustable node for adjusting noise/gain/PdB -one

Component list

C1	330pF	116RM331M050TT	ATC	-
C2	10nF	GRM155R71H103KA88D	MURATA	0402

Precautions

1. The chip is stored in a dry, nitrogen environment and used in an ultra-clean environment;
2. GaAs material is brittle and cannot touch the surface of the chip, so you must be careful when using it;
3. Chips are sintered with conductive glue or alloy (the alloy temperature cannot exceed 300°C, and the time cannot exceed 30 seconds) to make it fully grounded;
4. The gap between the microwave port of the chip and the substrate should not exceed 0.05mm. Use $\Phi 25\mu\text{m}$ double gold wire for bonding. The recommended length of gold wire is 250~400 μm ;
5. The chip is sensitive to static electricity, so pay attention to anti-static during storage and use.